

A METHOD OF IMPROVING ADHESION OF CAP OXIDE TO NANOPOROUS SILICA FOR INTEGRATED CIRCUIT FABRICATION

ABSTRACT OF THE DISCLOSURE

5       A method of improving adhesion of a cap oxide to nanoporous silica for integrated circuit fabrication. In one embodiment, the method comprises several steps. The first step is to receive a wafer in a deposition chamber. Then a porous layer of material is deposited on the wafer. Next, a portion of the porous layer is densified in order to make it more compatible for adhesion to a cap layer. Finally, a  
10      cap layer is deposited onto the porous layer.

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